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#### Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

### Listing of Claims:

Claim 1 (Original) A method for continuously preparing a silicon oxide powder, comprising the sups of:

feeding a raw material powder mixture containing silicon dioxide powder into a reaction furnace,

heating the mixture in the furnace in an inert gas or in vacuum to a temperature of 1,100 to 1,600°C to produce a silicon oxide gas,

introducing the silicon oxide gas into a cooling chamber through a transfer conduit which is maintained at a temperature of from higher than 1,000°C to 1,300°C, thereby causing silicon oxide to deposit on a surface of a substrate which is disposed and cooled in the cooling chamber, and

continuously recovering the silicon oxide deposit.

Claim 2 (Original) The method of claim 1 wherein the raw material powder mixture is a mixture comprised of a silicon dioxide powder and a metal silicon powder.

Claim 3 (Cancelled)

Claim 4 (New) The method of claim 1 wherein the raw material powder mixture is a mixture comprised of a silicon dioxide powder and a reducing powder therefor.

Claim 5 (New) The method of claim 1 wherein the raw material powder mixture is a mixture comprised of a silicon dioxide powder and a carbon-containing powder.

Claim 6 (New) A method according to claim 1, wherein heating the mixture in the furnace is to a temperature of 1,200 to 1,500°C.

Claim 7 (New) A method according to claim 1, wherein when heating the mixture in the furnace, the furnace is under vacuum

Claim 8 (New) A method according to claim 1, wherein the transfer conduit is maintained at 1,100 to 1,200°C.

Claim 9 (New) A method according to claim 1, wherein the substrate is cooled to 200 to 500°C.

Claim 10 (New) A method according to claim 1, wherein the substrate is cooled to 300 to 400°C.

Claim 11 (New) A method according to claim 1, wherein recovering the silicon oxide deposit is performed by a scraper.